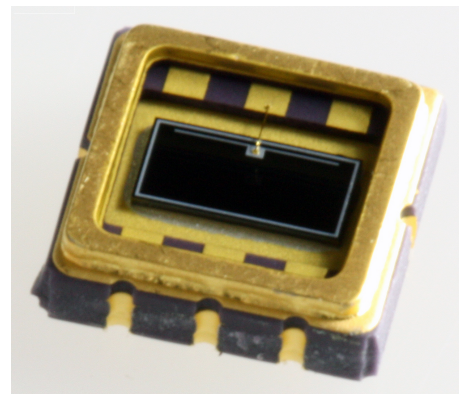


## Sensitivity Wavelength Range: 250-1100nm

The MT03-029 is a rectangular (1.30 x 2.80) 3.6mm<sup>2</sup> active area Silicon Photodiode in a surface mount package with clear epoxy encapsulation. It is designed for applications requiring high red and near infrared (NIR) light sensitivity.



### Features

- > Ultra Low Noise
- > High Shunt Resistance
- > Wide Dynamic Range
- > Broadband Spectral Coverage

### Applications

- > Colorimeters
- > Photometers
- > Spectroscopy Equipment
- > Fluorescence

## Absolute Maximum Ratings

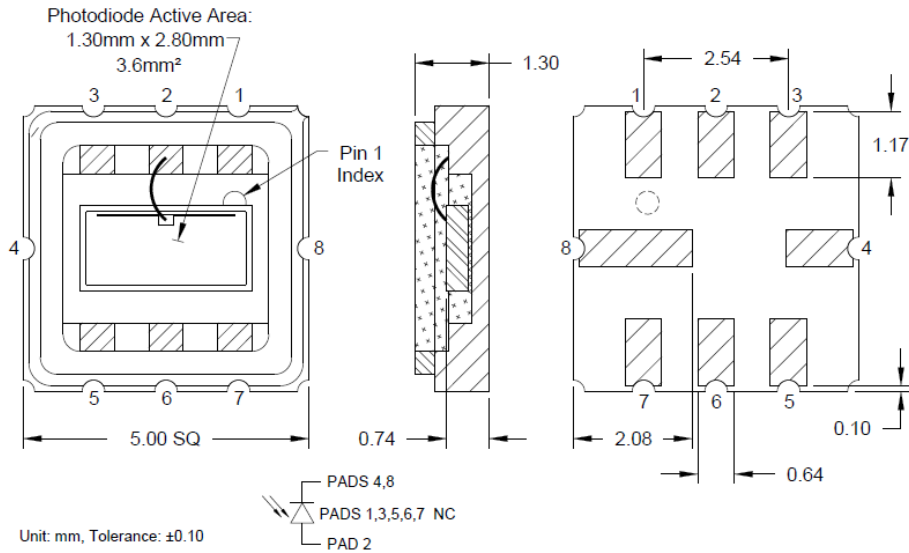


Items	Symbol	Rating	Unit
Reverse Voltage	V <sub>R</sub>	50	V
Operating Temperature Range	T <sub>opr</sub>	-40 ~ +100	°C
Storage Temperature Range	T <sub>stg</sub>	-55 ~ +125	°C
Reflow Soldering Temperature	T <sub>ls</sub>	250	°C

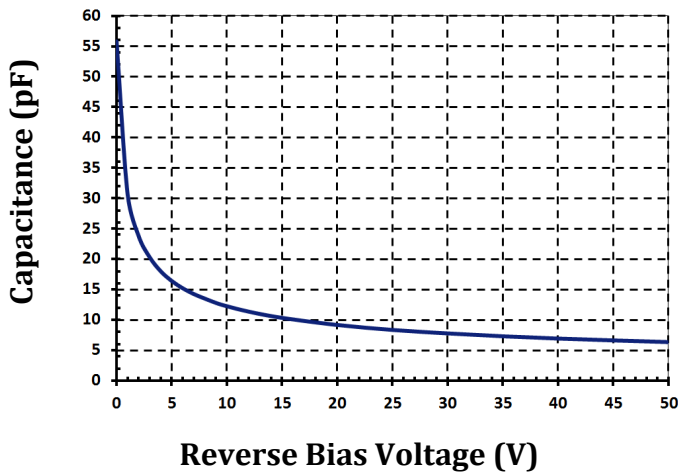
## Electrical & Optical Characteristics (T<sub>a</sub> = 23°C)

Items	Symbol	Conditions	MIN	TYP	MAX	Unit
Dark Current	I <sub>d</sub>	V <sub>R</sub> =5V	--	0.2	1.0	nA
Breakdown Voltage	V <sub>(BR)</sub>	I <sub>R</sub> =10μA	50	--	--	V
Spectral Sensitivity	λ	--	--	250-1100	--	nm
Peak Sensitivity	λ <sub>p</sub>	--	--	940	--	nm
Wavelength Responsivity	R	V <sub>R</sub> =0V, λ=633nm	--	0.45	--	A/W
Responsivity	R	V <sub>R</sub> =0V, λ=950nm	--	0.64	--	A/W
Response Time @808nm	T <sub>r</sub>	R <sub>L</sub> =50Ω, V <sub>R</sub> =5V	--	50	--	ns
Junction Capacitance	C <sub>j</sub>	@ 1MHz, V <sub>R</sub> =0V	--	60	--	pF
Junction Capacitance	C <sub>j</sub>	@ 1MHz, V <sub>R</sub> =5V	--	18	22	pF
Shunt Resistance	R <sub>sh</sub>	V <sub>R</sub> =10mV	700	1000	--	MΩ

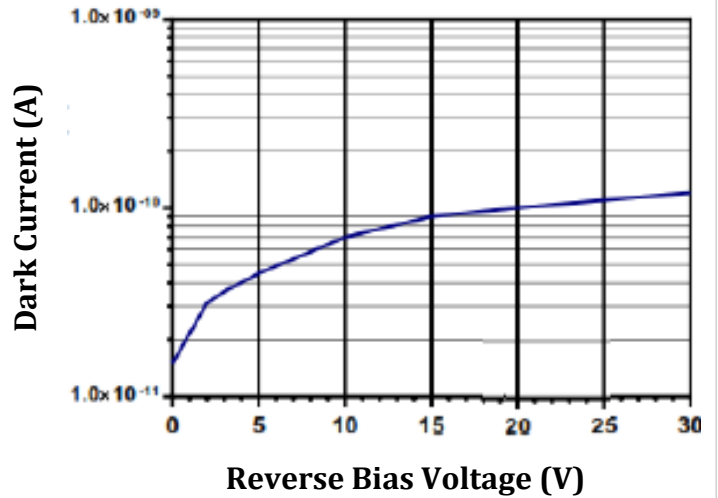
**SMD Package Dimensions (8 Pad)**



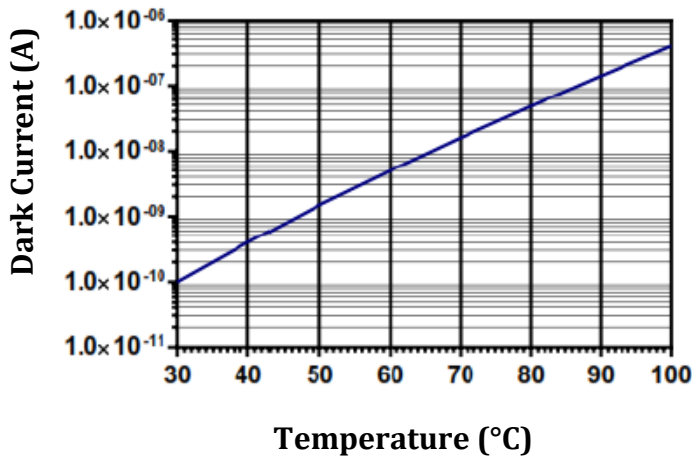
**Capacitance vs Reverse Bias**



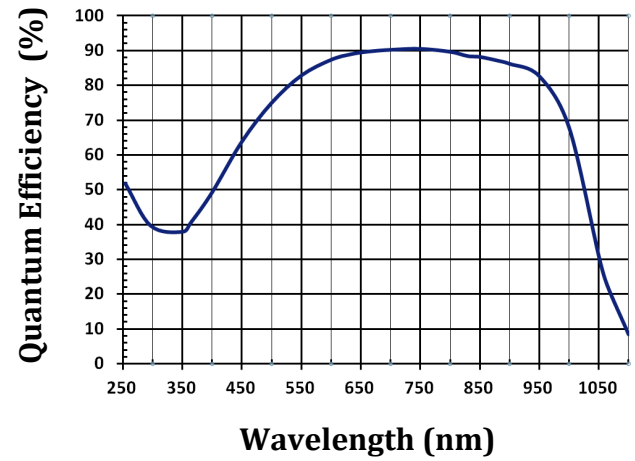
**Dark Current vs Reverse Bias (23°C)**



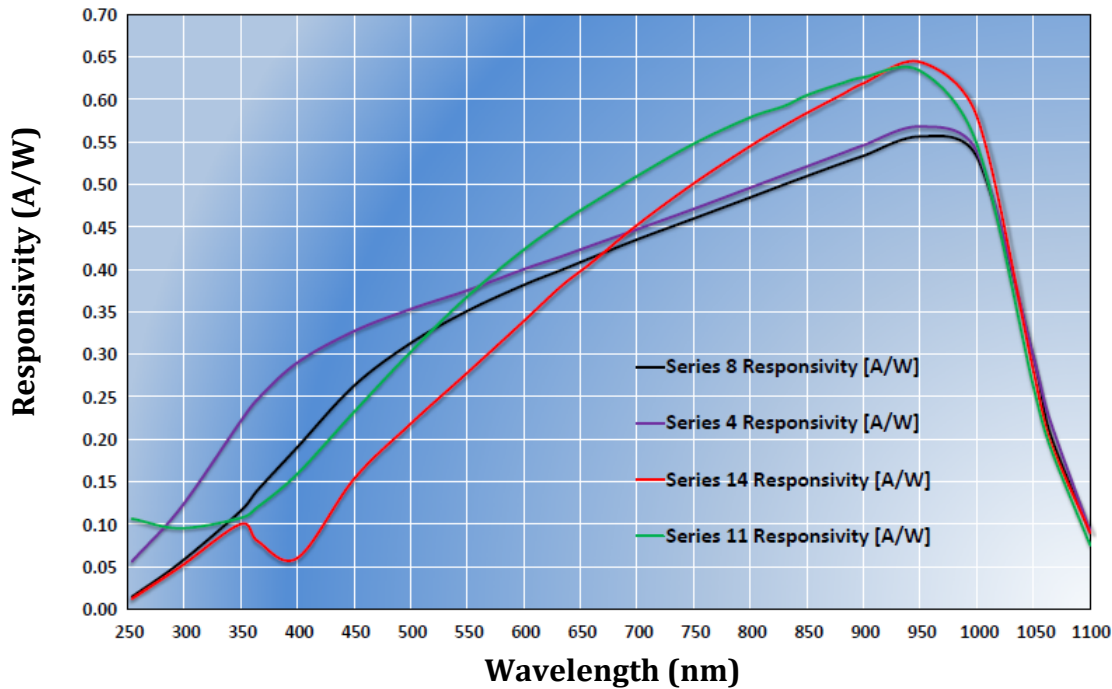
Dark Current vs Temperature ( $V_r=10V$ )



Series 11 Quantum Efficiency (23°C)



Photodiode Responsivity by Series



The information contained herein is subject to change without notice.

2019-06